

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SD2121(L)/(S)

Silicon NPN Epitaxial

RENESAS

ADE-208-925 (Z)

1st. Edition

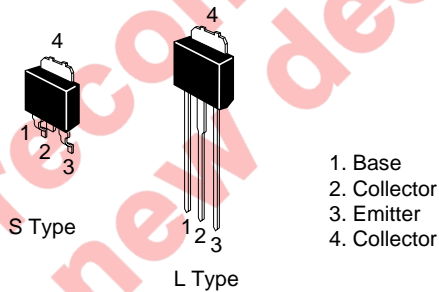
September 2000

Application

Low frequency power amplifier complementary pair with 2SB1407(L)/(S)

Outline

DPAK



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Rated	Unit
Collector to base voltage	V_{CBO}	35	V
Collector to emitter voltage	V_{CEO}	35	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_{C}	2.5	A
Collector peak current	$I_{\text{C(peak)}}$	3	A
Collector power dissipation	P_{C}^{*1}	18	W
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note: 1. Value at $T_{\text{C}} = 25^\circ\text{C}$.

2SD2121(L)/(S)

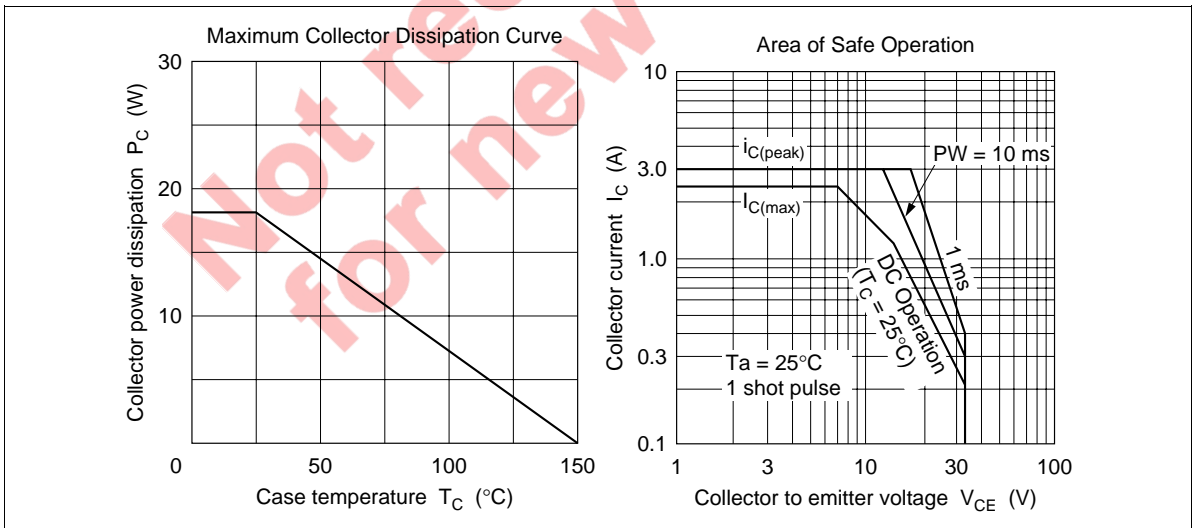
Electrical Characteristics (Ta = 25°C)

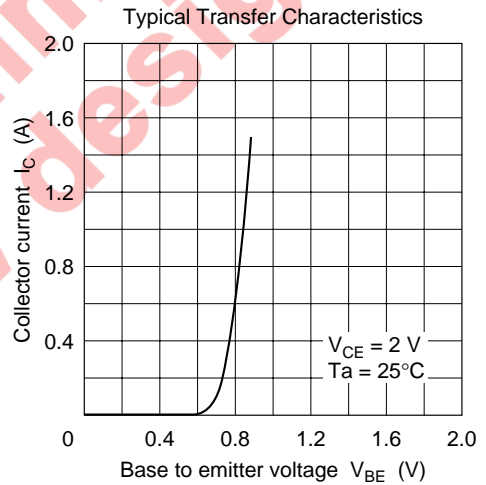
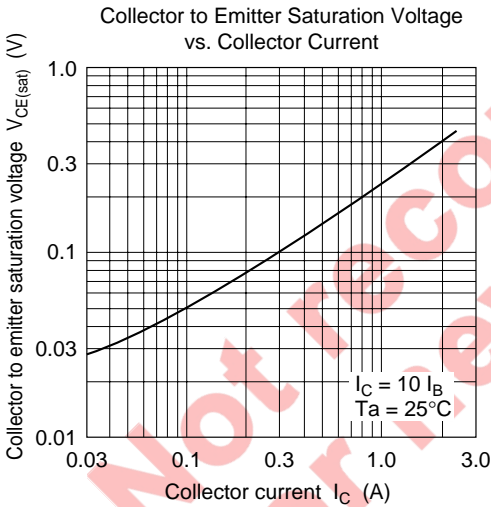
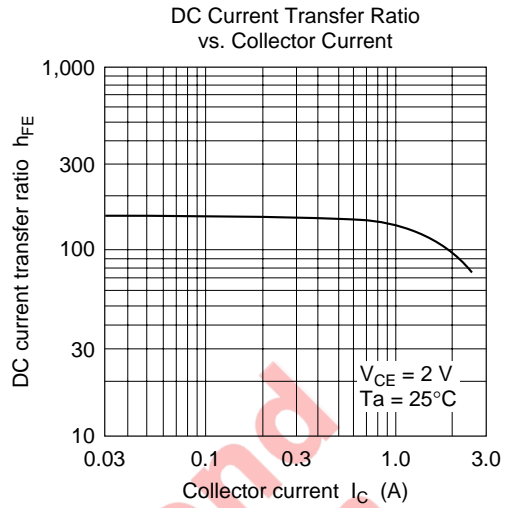
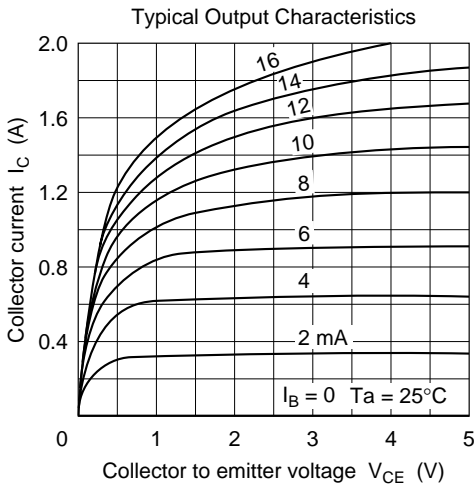
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	35	—	—	V	$I_C = 1 \text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	35	—	—	V	$I_C = 10 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 1 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	20	μA	$V_{CB} = 35 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320		$V_{CE} = 2 \text{ V}, I_C = 0.5 \text{ A}^{*2}$
	h_{FE2}	20	—	—		$V_{CE} = 2 \text{ V}, I_C = 1.5 \text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	1.5	V	$V_{CE} = 2 \text{ V}, I_C = 1.5 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 2 \text{ A}, I_B = 0.2 \text{ A}^{*2}$

Notes: 1. The 2SD2121(L)/(S) is grouped by h_{FE1} as follows.

B	C	D
60 to 120	100 to 200	160 to 320

2. Pulse test.





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